Preferred Device

NPN Silicon Planar Epitaxial Transistor

This NPN Silicon Epitaxial transistor is designed for use in industrial and consumer applications. The device is housed in the SOT-223 package which is designed for medium power surface mount applications.

SOT-223 package ensures level mounting, resulting in improved thermal conduction, and allows visual inspection of soldered joints. The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die.

Features

- High Current: 2.0 A
- The SOT-223 package can be soldered using wave or reflow
- Available in 12 mm Tape and Reel
 Use PZT651T1 to order the 7 inch/1000 unit reel
 Use PZT651T3 to order the 13 inch/4000 unit reel
- PNP Complement is PZT751T1
- Pb-Free Package is Available

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current	I _C	2.0	Adc
Total Power Dissipation @ T _A = 25°C (Note 1)	P _D	0.8	W
Derate above 25°C		6.4	mW/°C
Storage Temperature Range	T _{stg}	-65 to 150	°C
Junction Temperature	TJ	150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance from Junction-to-Ambient in Free Air	$R_{ heta JA}$	156	°C/W
Maximum Temperature for Soldering Purposes	T_L	260	°C
Time in Solder Bath		10	Sec

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

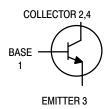
 Device mounted on a FR-4 glass epoxy printed circuit board using minimum recommended footprint.



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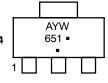
SOT-223 PACKAGE HIGH CURRENT NPN SILICON TRANSISTOR SURFACE MOUNT



MARKING DIAGRAM



TO-261AA CASE 318E-04 STYLE 1



A = Assembly Location

Y = Year WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

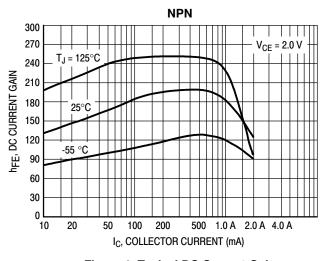
Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage $(I_C = 10 \text{ mAdc}, I_B = 0)$	V _(BR) CEO	60	-	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	V _(BR) CBO	80	-	Vdc
Emitter-Base Breakdown Voltage $(I_E = 10 \mu Adc, I_C = 0)$	V _{(BR)EBO}	5.0	-	Vdc
Base-Emitter Cutoff Current (V _{EB} = 4.0 Vdc)	I _{EBO}	-	0.1	μAdc
Collector-Base Cutoff Current (V _{CB} = 80 Vdc, I _E = 0)	I _{CBO}	-	100	nAdc
ON CHARACTERISTICS (Note 2)	·			
DC Current Gain $ \begin{array}{l} (I_C = 50 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}) \\ (I_C = 500 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}) \\ (I_C = 1.0 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc}) \\ (I_C = 2.0 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc}) \end{array} $	h _{FE}	75 75 75 40	- - - -	-
Collector-Emitter Saturation Voltages ($I_C = 2.0 \text{ Adc}$, $I_B = 200 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}$, $I_B = 100 \text{ mAdc}$)	V _{CE(sat)}	- -	0.5 0.3	Vdc
Base-Emitter Voltages (I _C = 1.0 Adc, V _{CE} = 2.0 Vdc)	V _{BE(on)}	-	1.0	Vdc
Base-Emitter Saturation Voltage (I _C = 1.0 Adc, I _B = 100 mAdc)	V _{BE(sat)}	-	1.2	Vdc
Current-Gain — Bandwidth (I _C = 50 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)	f _T	75	-	MHz

^{2.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%

ORDERING INFORMATION

Device	Package	Shipping [†]
PZT651T1	SOT-223	1000 / Tape and Reel
PZT651T1G	SOT-223 (Pb-Free)	1000 / Tape and Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





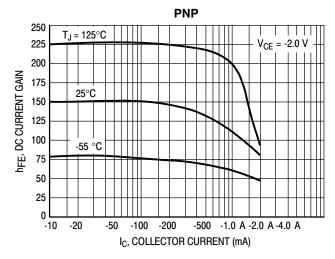


Figure 2. Typical DC Current Gain

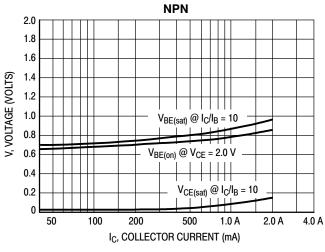


Figure 3. On Voltages

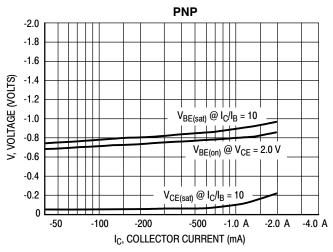


Figure 4. On Voltages

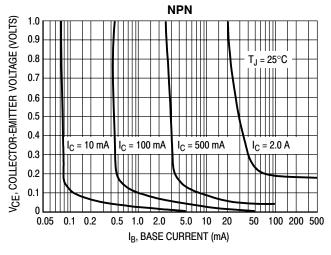


Figure 5. Collector Saturation Region

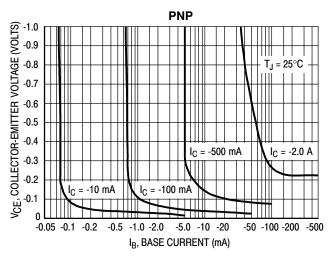
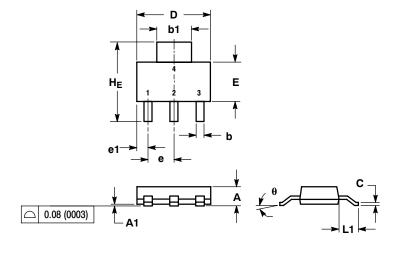


Figure 6. Collector Saturation Region

PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE L

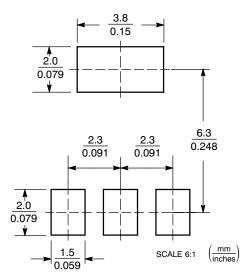


- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.020	0.061	0.102	0.0008	0.0024	0.0040
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
С	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
е	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°

- STYLE 1: PIN 1. BASE
 - 2. COLLECTOR 3. EMITTER
 - COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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